

# CMOS Comparator Design

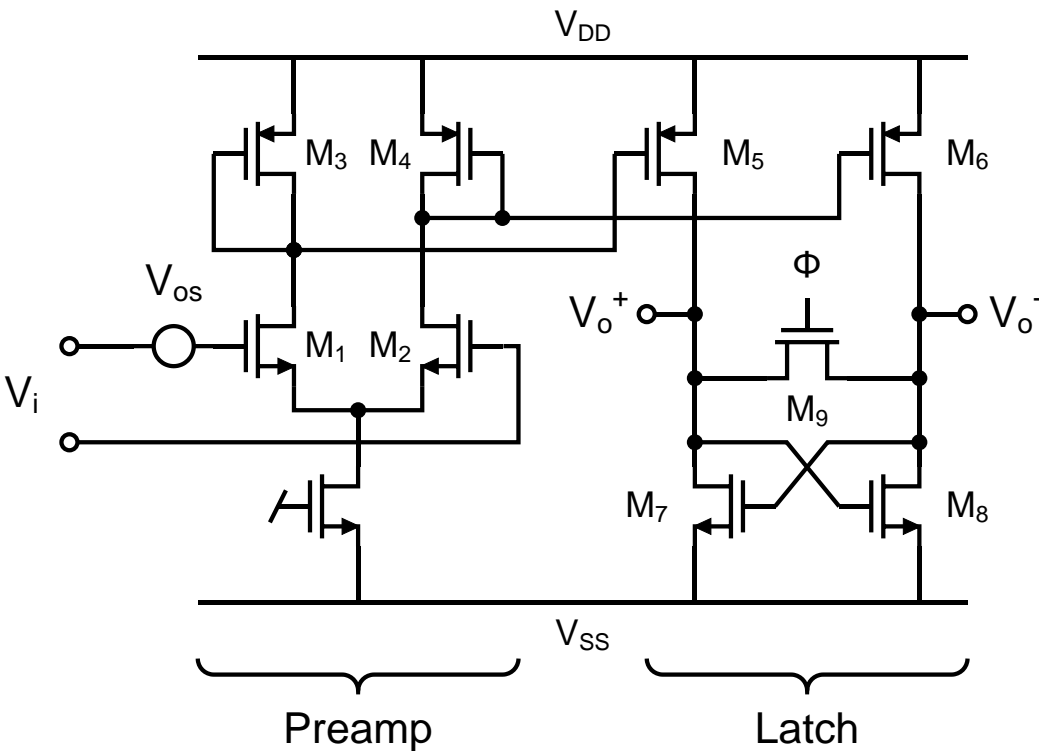
## *Extra Slides*

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# Comparator Design Considerations

- ❑ Comparator =
  - Preamp (optional)
  - + Reference Subtraction (optional for single-bit case)
  - + Regenerative Latch
  - +Static Latch to hold outputs (optional)
- ❑ Design Considerations
  - Accuracy (dynamic and static offset, noise, resolution)
  - Settling time (tracking BW, regeneration speed)
  - Sensitivity/resolution (gain)
  - Metastability (ability to make correct decisions)
  - Overdrive recovery (memory)
  - Power consumption

# An Example CMOS Comparator

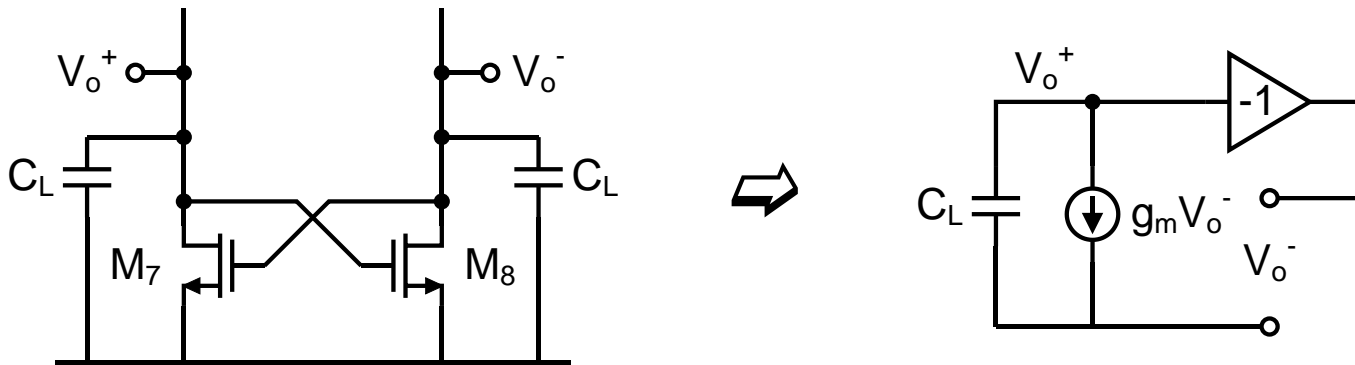


$V_{os}$  originates from:

- Preamp input pair mismatch ( $V_{th}, W/L$ )
- PMOS loads and current mirror
- Latch offset
- Charge-Injection  
clock-feedthru imbalance of the reset switch (M9)
- Clock routing
- Parasitics



# Regeneration Speed – Linear Model

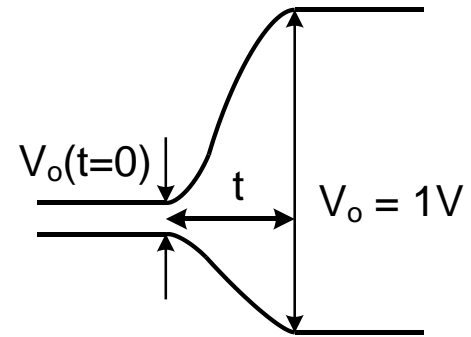
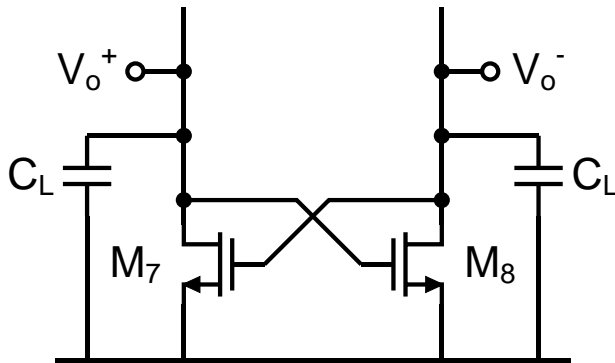


$$\begin{cases} V_o^+ = -V_o^- \\ V_o^+ = -g_m \cdot V_o^- / sC_L \end{cases} \Rightarrow \begin{pmatrix} 1 & 1 \\ 1 & g_m/sC_L \end{pmatrix} \begin{pmatrix} V_o^+ \\ V_o^- \end{pmatrix} = 0$$

$$\Delta(s) = g_m/sC_L - 1 = 0 \Rightarrow s_p = g_m/C_L, \text{ single RHP pole}$$

$$V_o(t > 0) = V_o(t = 0) \cdot \exp(t \cdot g_m/C_L)$$

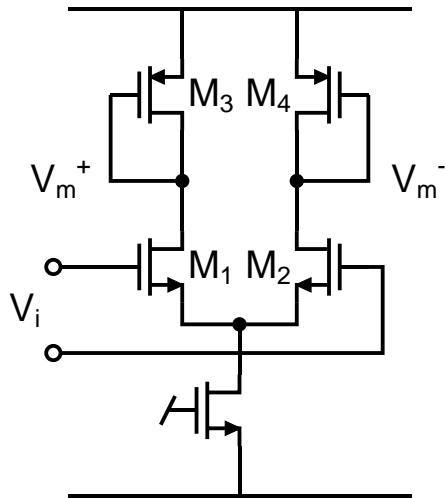
# Reg. Speed – Linear Model



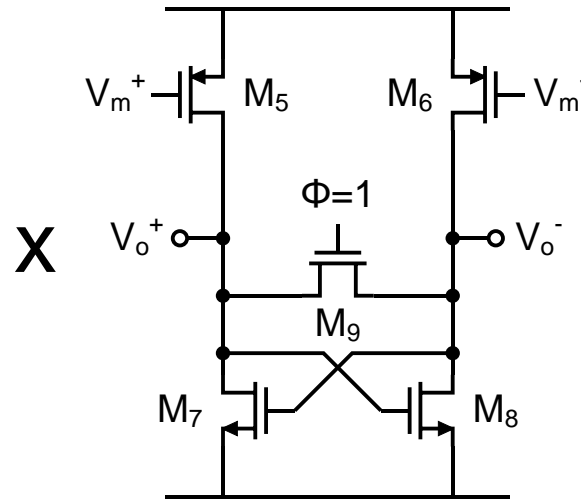
$V_o$	$V_o(t=0)$	$t/(C_L/g_m)$
1V	100mV	2.3
1V	10mV	4.6
1V	1mV	6.9
1V	100 $\mu$ V	9.2

$$t = \frac{C_L}{g_m} \cdot \ln \left[ \frac{V_o(t)}{V_o(t=0)} \right]$$

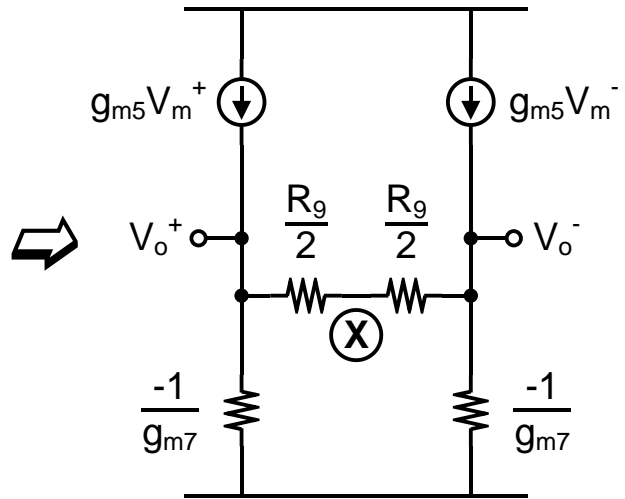
# Reg. Speed – Linear Model



$$|A_{V1}| = \frac{g_{m1}}{g_{m3}}$$



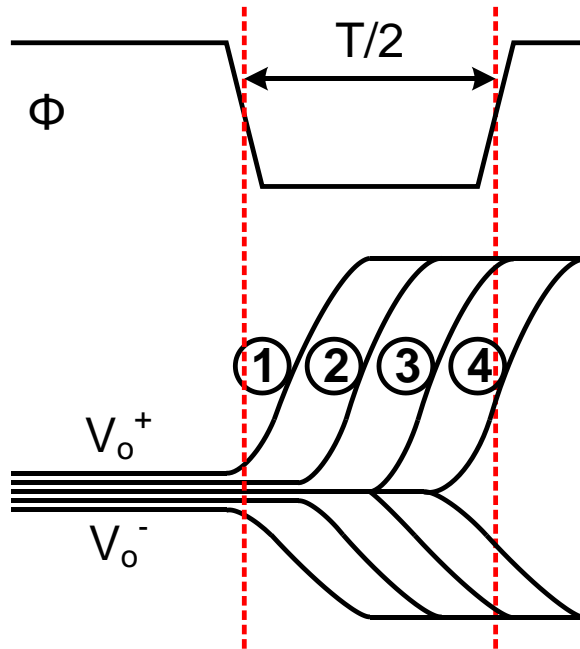
$$|A_{V2}| = \frac{g_{m5}R_9}{2 - g_{m7}R_9}, \quad \frac{R_9}{2} < \frac{1}{g_{m7}} \text{ to be amplifier.}$$



$$V_o(0) = V_i(0) \cdot A_V = V_i(0) \cdot A_{V1} A_{V2}$$

$$V_o(t) = V_i(0) \cdot A_{V1} A_{V2} \cdot \exp(t \cdot g_m / C_L)$$

# Comparator Metastability



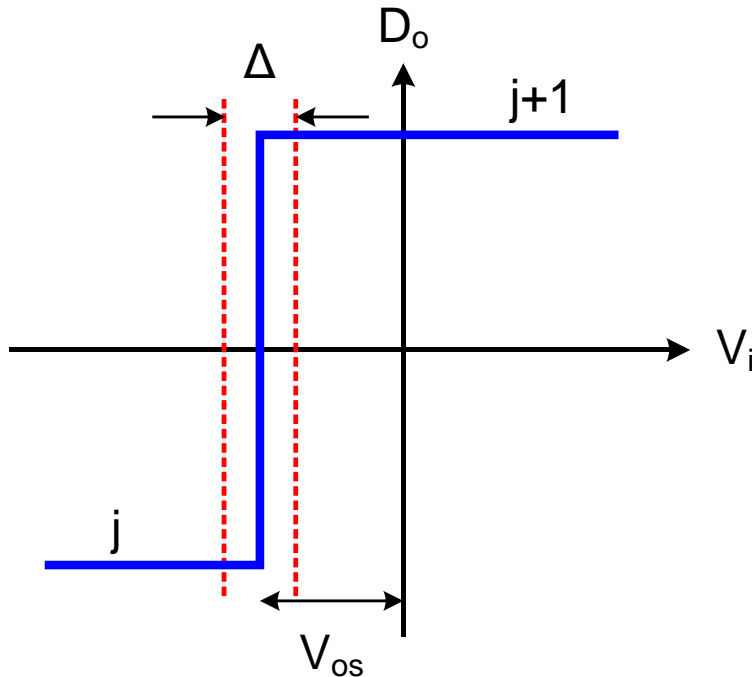
$$V_o(t) = V_i(0) \cdot A_{V1} A_{V2} \cdot \exp(t \cdot g_m / C_L)$$

Curve	$A_{V1}A_{V2}$	$V_i(t=0)$
①	10	10 mV
②	10	1 mV
③	10	100 $\mu$ V
④	10	10 $\mu$ V

Comparator fails to produce valid logic outputs within  $T/2$  when input falls into a region that is sufficiently close to the comparator threshold



# Comparator Metastability



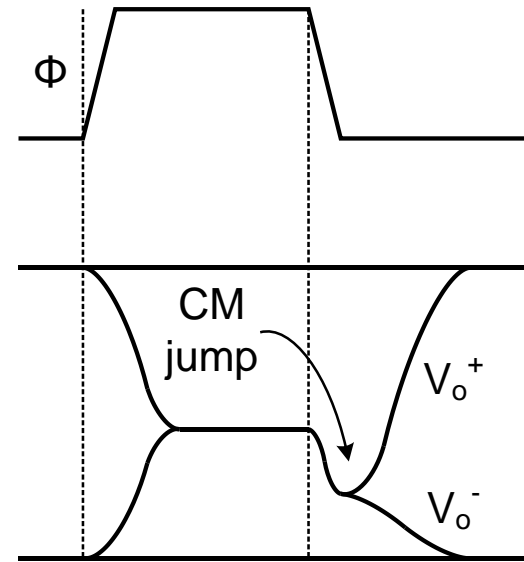
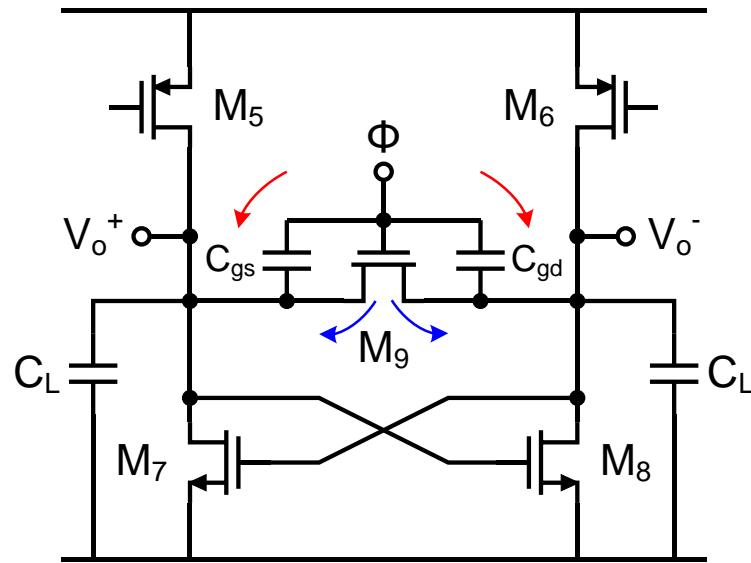
Assuming that the input is uniformly distributed over  $V_{FS}$ , then

$$\text{BER} = \frac{\Delta}{1\text{LSB}}$$

$$V_o(t) = V_i(0) \cdot A_{V1} A_{V2} \cdot \exp(t \cdot g_m / C_L)$$

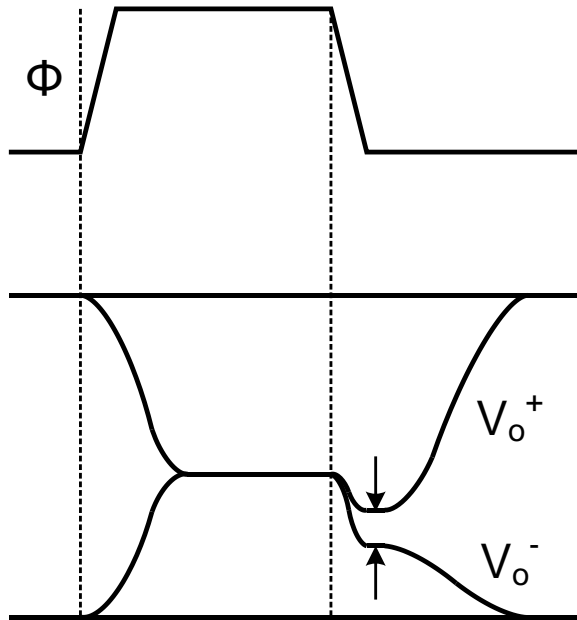
- Cascade preamp stages (typical flash comparator has 2-3 pre-amp stages)
- Use pipelined multi-stage latches; pre-amp can be pipelined too

# Charge-Injection and Clock-Feedthrough in Latch



- Charge injection (CI) and clock-feedthrough (CF) introduce CM jump in  $V_o^+$  and  $V_o^-$
- Dynamic latches are more susceptible to CI and CF errors

# Dynamic Offset of a Latch



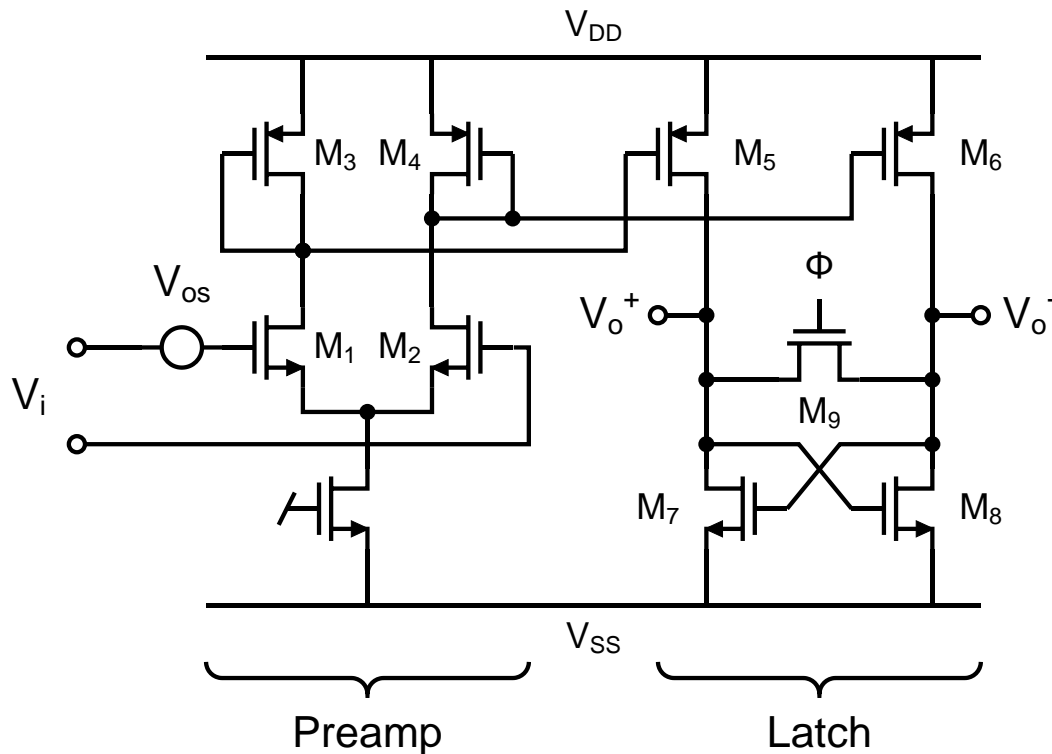
Dynamic offset derives from:

- Imbalanced CI and CF
- Imbalanced load capacitance
- Mismatch b/t  $M_7$  and  $M_8$
- Mismatch b/t  $M_5$  and  $M_6$
- Clock routing

$\left. \begin{array}{l} 0.5V \text{ CM jump} \\ 10\% \text{ imbalance} \end{array} \right\} \Rightarrow 50mV \text{ offset}$

Dynamic offset is usually the dominant offset error in latches

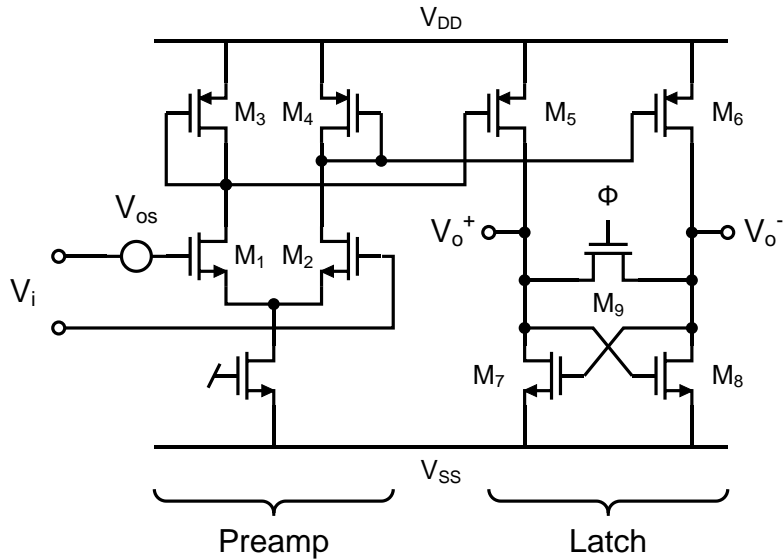
# Typical CMOS Comparator



- Input-referred latch offset gets divided by the gain of PA
- Preamp introduces its own offset (mostly static due to  $V_{th}$ ,  $W$ , and  $L$  mismatches)
- PA also reduces kickback noise

Kickback noise disturbs reference voltages, must settle before next sample

# Comparator Offset



Differential pair mismatch:

$$V_{os}^2 = (\Delta V_{th})^2 + \frac{1}{4} V_{ov}^2 \left( \frac{\Delta \frac{W}{L}}{\frac{W}{L}} \right)^2$$

$$|A_{V1}| = \frac{g_{m1}}{g_{m3}}$$

$$|A_{V2}| = \frac{g_{m5} R_9}{2 - g_{m7} R_9}$$

Total input-referred comparator offset:

$$V_{os}^2 = V_{os,12}^2 + \frac{V_{os,34}^2 + V_{os,56}^2}{A_{V1}^2} + \frac{V_{os,78}^2}{A_{V1}^2 A_{V2}^2} + \frac{V_{os,dyn}^2}{A_{V1}^2 A_{V2}^2}$$

# Recall: Matching Properties

Suppose parameter  $P$  of two rectangular devices has a mismatch error of  $\Delta P$ . The variance of parameter  $\Delta P$  b/t the two devices is

$$\sigma^2(\Delta P) = \frac{A_P^2}{WL} + S_P^2 D^2,$$

1<sup>st</sup> term dominates  
for small devices

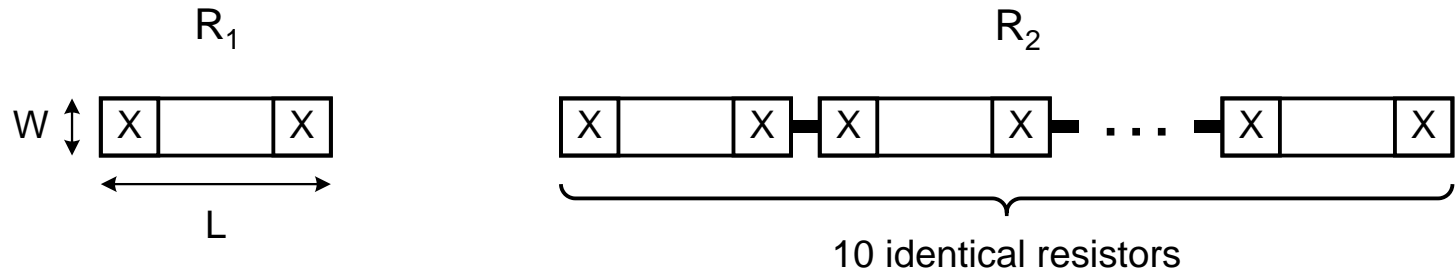
where,  $W$  and  $L$  are the effective width and length,  $D$  is the distance

$$\text{Threshold: } \sigma^2(V_{th}) = \frac{A_{V_{th}}^2}{WL} + S_{V_{th}}^2 D^2$$

$$\text{Current factor: } \frac{\sigma^2(\beta)}{\beta^2} = \frac{A_\beta^2}{WL} + S_\beta^2 D^2$$

Ref: M. J. M. Pelgrom, et al., "Matching properties of MOS transistors," *IEEE Journal of Solid-State Circuits*, vol. 24, pp. 1433-1439, issue 5, 1989.

# Recall: Device Sizing for Mismatch



$$R_1 = R_S \cdot \frac{L}{W} \text{ with std } \sigma_{R1}$$

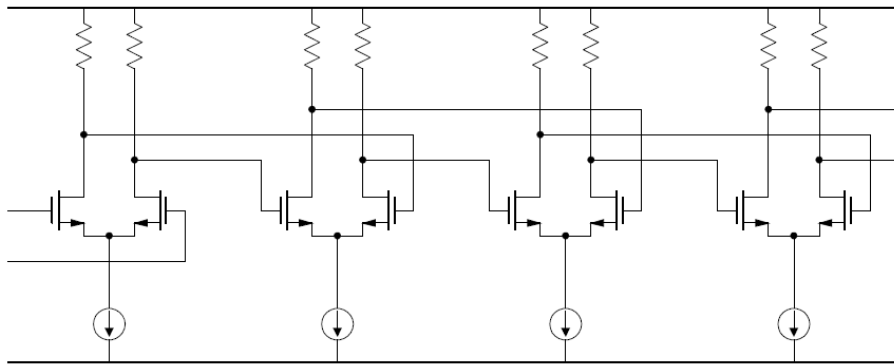
$$R_2 = R_S \cdot 10 \left( \frac{L}{W} \right) = 10R_1 \text{ with std } \sigma_{R2},$$

$$\sigma_{R2}^2 = \sum_{j=1}^{10} \sigma_{R_j}^2 = 10\sigma_{R1}^2 \Rightarrow \sigma_{R2} = \sqrt{10}\sigma_{R1}$$

$$\frac{\sigma_{R2}}{R_2} = \frac{\sqrt{10}\sigma_{R1}}{10R_1} = \frac{1}{\sqrt{10}} \left( \frac{\sigma_{R1}}{R_1} \right) \Rightarrow \frac{\sigma_R}{R} \propto \frac{1}{\sqrt{A}} = \frac{1}{\sqrt{WL}} \quad \text{“Spatial averaging”}$$

# Pre-amp Design

- A fully-differential gain-stage
  - Avoid or use simple CMFB
  - Pre-amp gain reduces input referred offset due to the latch
  - Autozeroing techniques for offset storage and reduction
- Pre-amp open-loop gain vs tracking bandwidth trade-off
  - Multiple stages of pre-amp limit bandwidth
    - Optimum value of stages 2-4



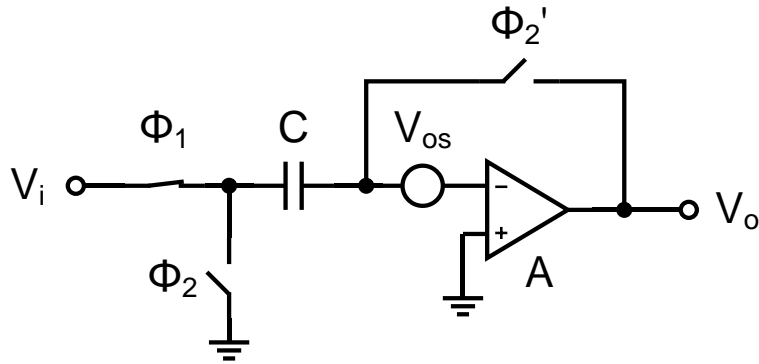
N stages:

$$|A_N(\omega)| = \left| \left( \frac{A_0}{1 + j \cdot \omega / \omega_0} \right)^N \right| = \left( \frac{A_0}{\sqrt{1 + (\omega / \omega_0)^2}} \right)^N$$

$$|A_N(\omega = \omega_{-3dB})| = \frac{A_0^N}{\sqrt{2}}, \quad \omega_{-3dB} = \omega_0 \sqrt{2^{\frac{1}{N}} - 1}$$



# Pre-amp (PA) Autozeroing

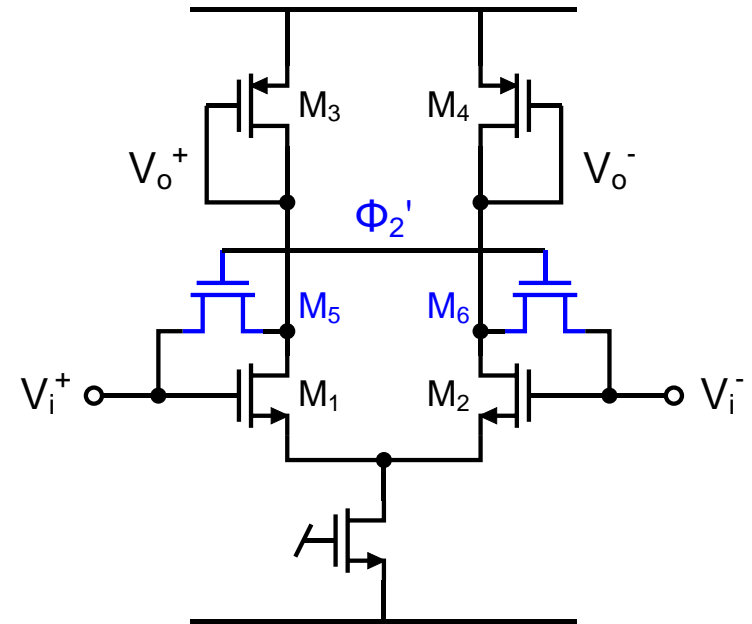


- Finite preamp gain :

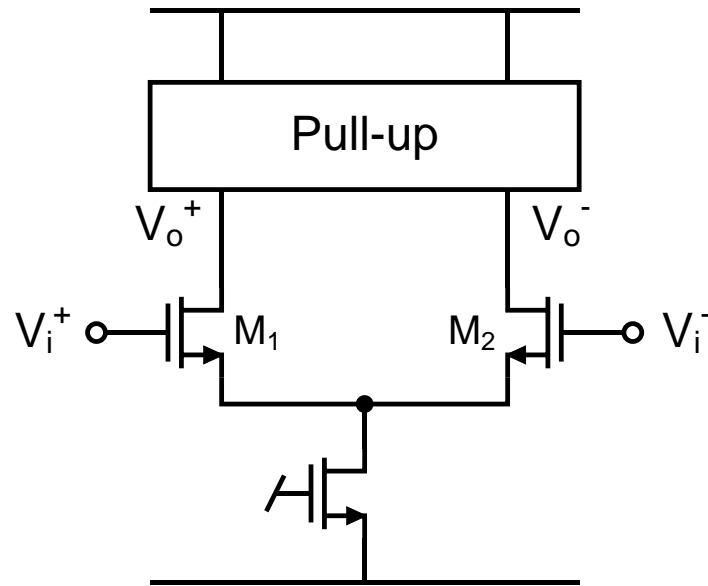
$$V_{OS,in} \approx \frac{V_{OS,pre-amp}}{A}$$

- For the overall comparator :

$$\sigma^2_{V_{OS,in}} \approx \frac{\sigma^2_{V_{OS,pre}}}{A^2_{pre}} + \frac{\sigma^2_{V_{OS,latch}}}{A^2_{pre}}$$



# Pre-amp Design: Pull-up load



- NMOS diode pull-up:

$$A_V = -\frac{g_{m1}}{g_{mL}} = -\sqrt{\frac{(W/L)_1}{(W/L)_L}}$$

- PMOS diode pull-up:

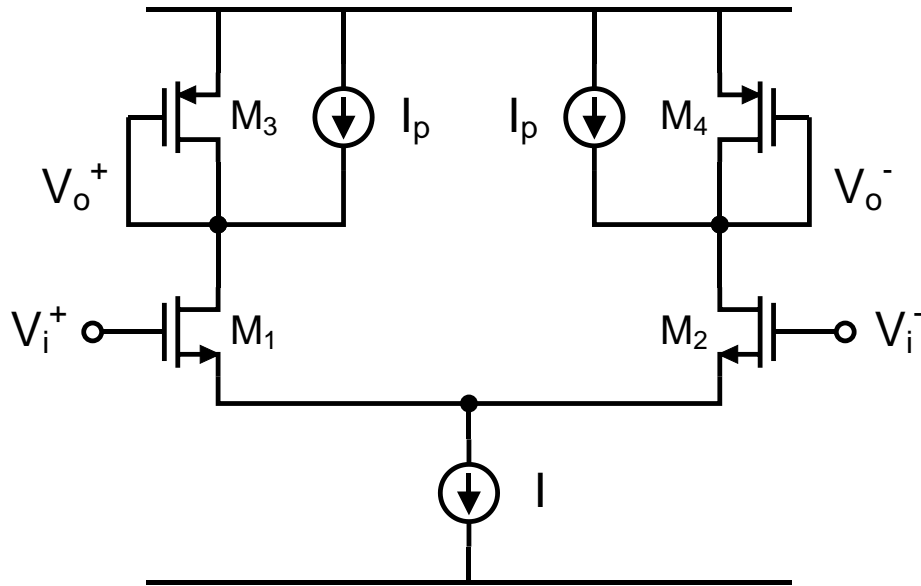
$$A_V = -\frac{g_{m1}}{g_{mL}} = -\sqrt{\frac{\mu_n (W/L)_1}{\mu_p (W/L)_L}}$$

- Resistor pull-up:

$$A_V = -g_{m1} \cdot R_L$$

- NMOS pull-up suffers from body effect, affecting gain accuracy
- PMOS pull-up is free from body effect, but subject to P/N mismatch
- Gain accuracy is the worst for resistive pull-up as resistors (poly, diffusion, well, etc.) don't track transistors; but it is fast!

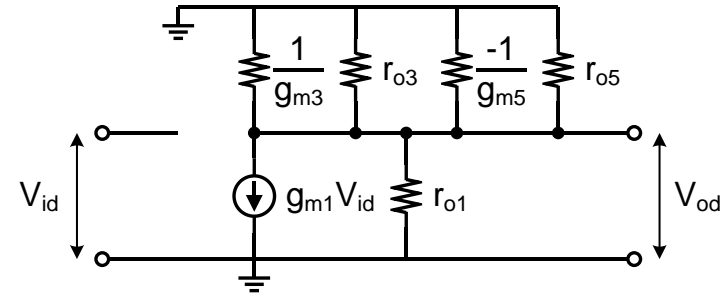
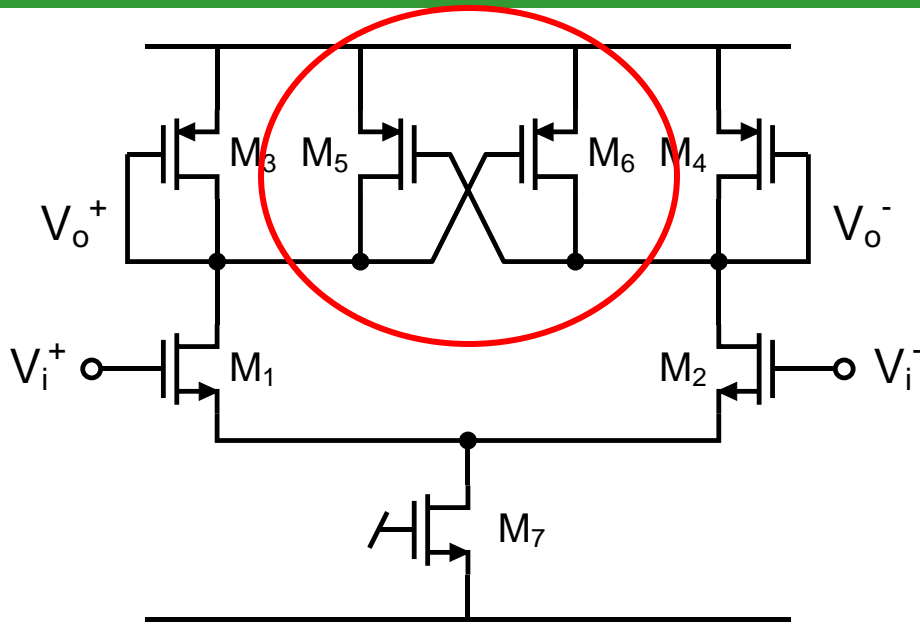
# Pre-amp Design: More Gain



$$A_V = -\frac{g_{m1}}{g_{m3}} \approx -\sqrt{\frac{\mu_n}{\mu_p} \left( \frac{I/2}{I/2 - I_p} \right) \frac{(W/L)_1}{(W/L)_3}}$$

- $I_p$  diverts current away from PMOS diodes ( $M_3$  &  $M_4$ ), reducing  $(W/L)_3$
- Higher gain without CMFB
- Needs biasing for  $I_p$
- $M_3$  &  $M_4$  may cut off for large  $V_{in}$ , resulting in a slow recovery

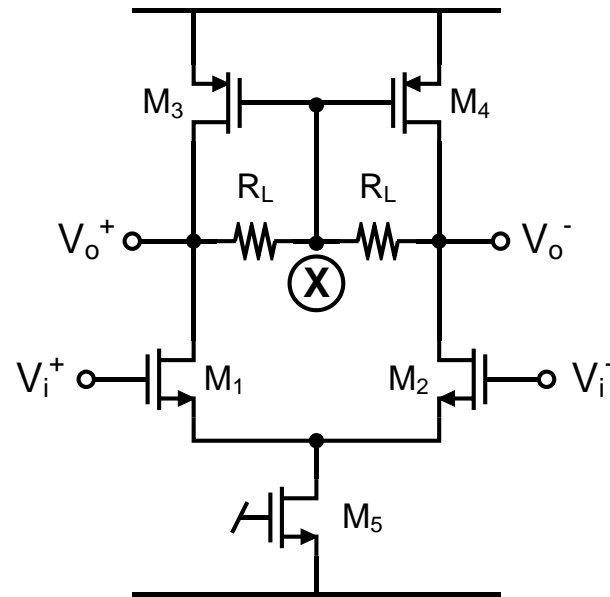
# Faster Settling Pre-amp



$$\text{DMgain: } A_V^{\text{dm}} = -g_{m1} \cdot \left[ \frac{1}{g_{m3}} \parallel \left( -\frac{1}{g_{m5}} \right) \parallel r_{o1} \parallel r_{o3} \parallel r_{o5} \right] \approx -\frac{g_{m1} r_{o1}}{3}$$

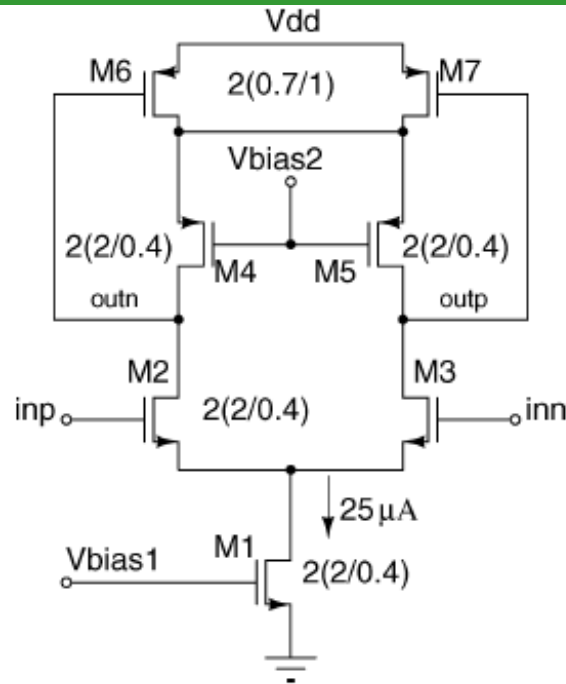
- NMOS diff-pair loaded with PMOS diodes and a PMOS cross-coupled latch
- High DM gain, low CM gain, good CMRR
- Simple, no CMFB required
- $(W/L)_{34} > (W/L)_{56}$  needs to be ensured for stability
- Ref: K. Bult and A. Buchwald, "An embedded 240-mW 10-b 50-MS/s CMOS ADC in 1-mm<sup>2</sup>," JSSC, vol. 32, pp. 1887-1895, issue 12, 1997.

# Pre-amp Example



- NMOS diff. pair loaded with PMOS diodes and resistors
- High DM gain, low CM gain, good CMRR
- Simple, no CMFB required
- Gain not well-defined
- Ref: B.-S. Song et al., "A 1 V 6 b 50 MHz current-interpolating CMOS ADC," in *Symp. VLSI Circuits*, 1999, pp. 79-80.

# Pre-amp Example

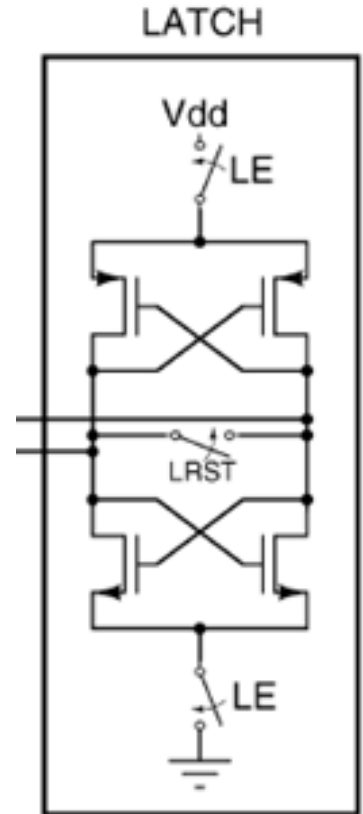


- NMOS diff. pair loaded with PMOS Current mirror
  - Simple CMFB circuit
- Gain is well-defined

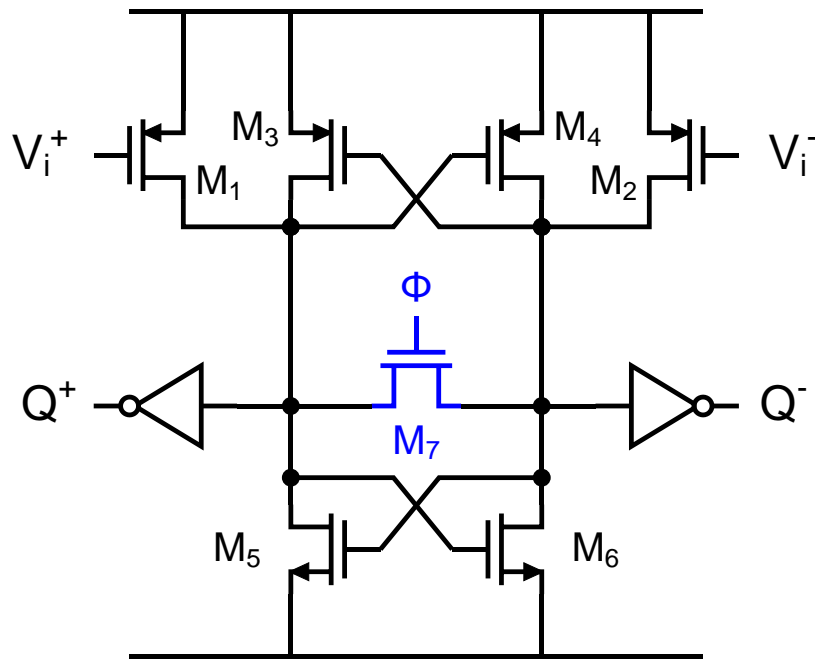
Ref: V. Srinivas, S. Pavan, A. Lachhwani, and N. Sasidhar, "A Distortion Compensating Flash Analog-to-Digital Conversion Technique," IEEE JSSC, vol. 41, no. 9, pp. 1959-1969, Sep. 2006.

# Latch Design

- Regenerative latches for faster settling
  - See lecture notes
- At least one cross-coupled regenerative core
  - Local positive feedback
  - Numerous methods for applying the input initial signal to regenerate upon
  - Latches can have large static and dynamic offsets
- Large Regenerative gain for resolving small inputs
  - Metastability (wrong or incomplete decisions) when latch can't make decision
  - Pre-amp can be used for amplifying the inputs (slower tracking BW)
- One size doesn't fit all applications
  - Speed vs power consumption trade-off



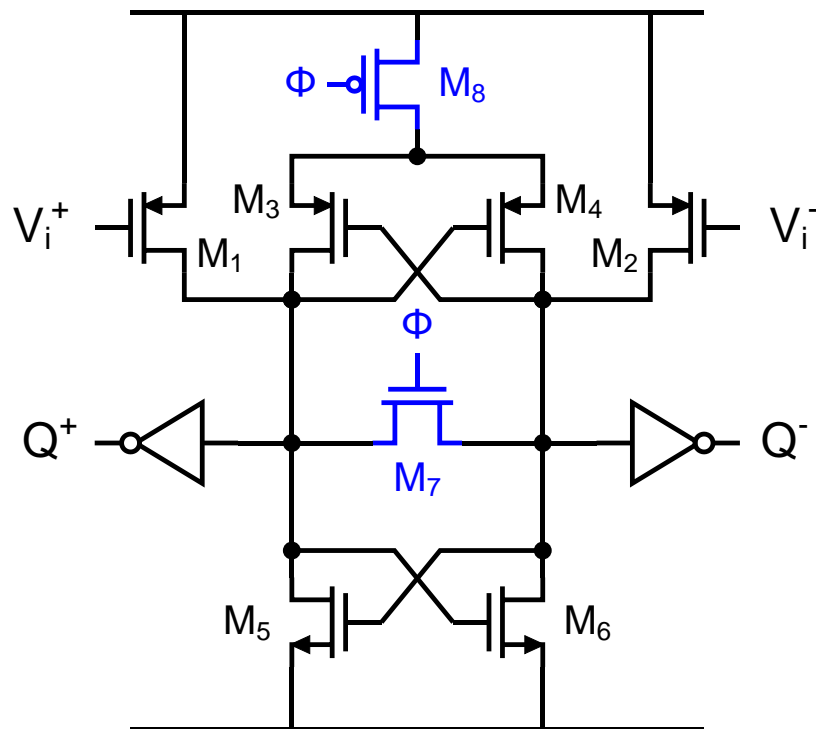
# Static Latch



- Active pull-up and pull-down  $\rightarrow$  full CMOS logic levels
- Very fast!
- $Q^+$  and  $Q^-$  are not well defined in reset mode ( $\Phi = 1$ )
- Large short-circuit current in reset mode
- Zero DC current after full regeneration
- Supply is very noisy

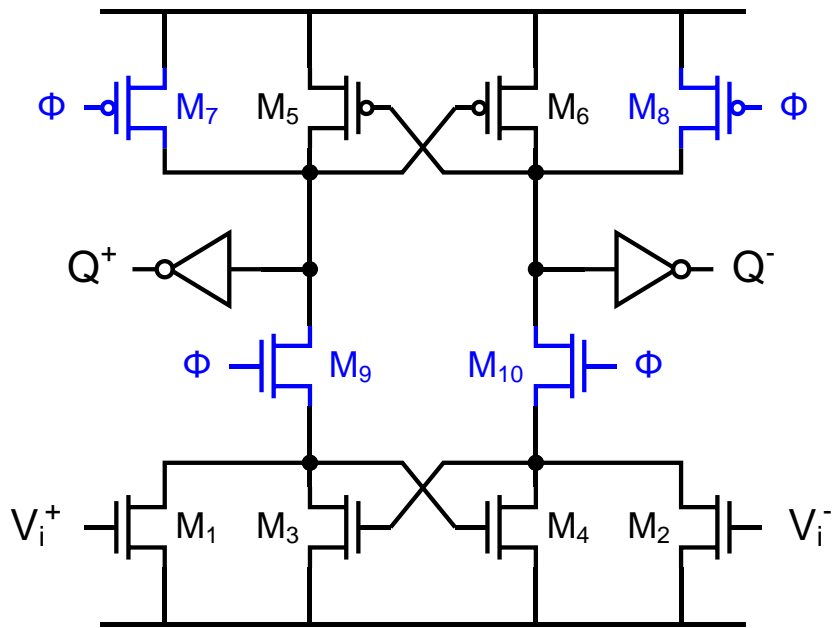


# Semi-Dynamic Latch



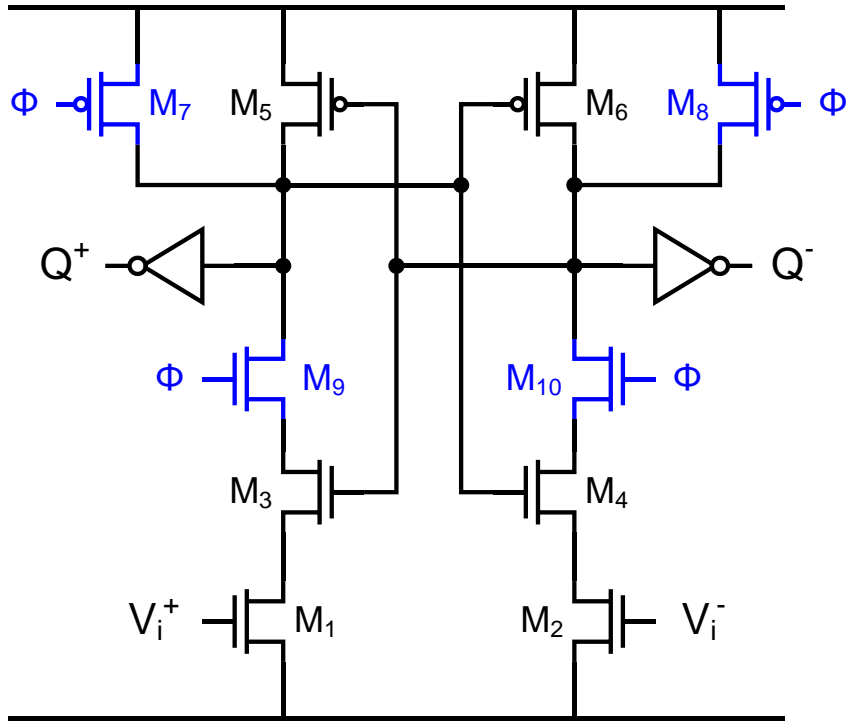
- Diode divider disabled in reset mode  
→ less short-circuit current
- Pull-up not as fast
- $Q^+$  and  $Q^-$  are still not well defined in reset mode ( $\Phi = 1$ )
- Zero DC current after full regeneration
- Supply still very noisy

# Dynamic Latch



- Zero DC current in reset mode
- $Q^+$  and  $Q^-$  are both reset to “0”
- Full logic level after regeneration
- Slow

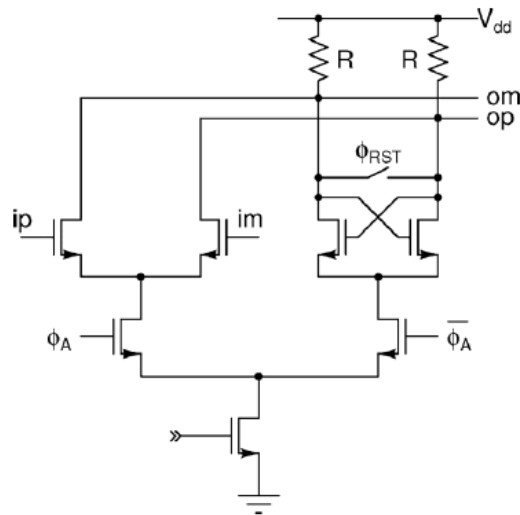
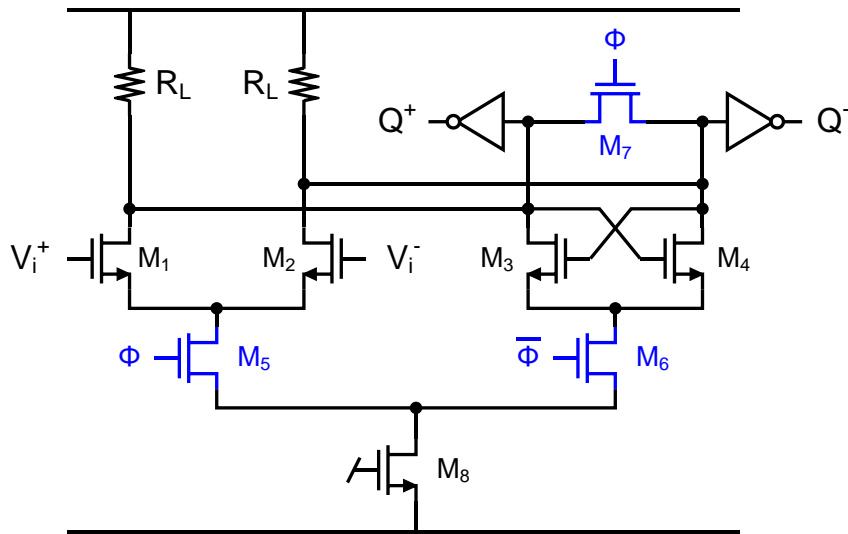
# Dynamic Latch 2



- Zero DC current in reset mode
- $Q^+$  and  $Q^-$  are both reset to "0"
- Full logic level after regeneration
- Slow

Ref: T. B. Cho and P. R. Gray, "A 10 b, 20 Msample/s, 35 mW pipeline A/D converter," *JSSC*, vol. 30, pp. 166-172, issue 3, 1995.

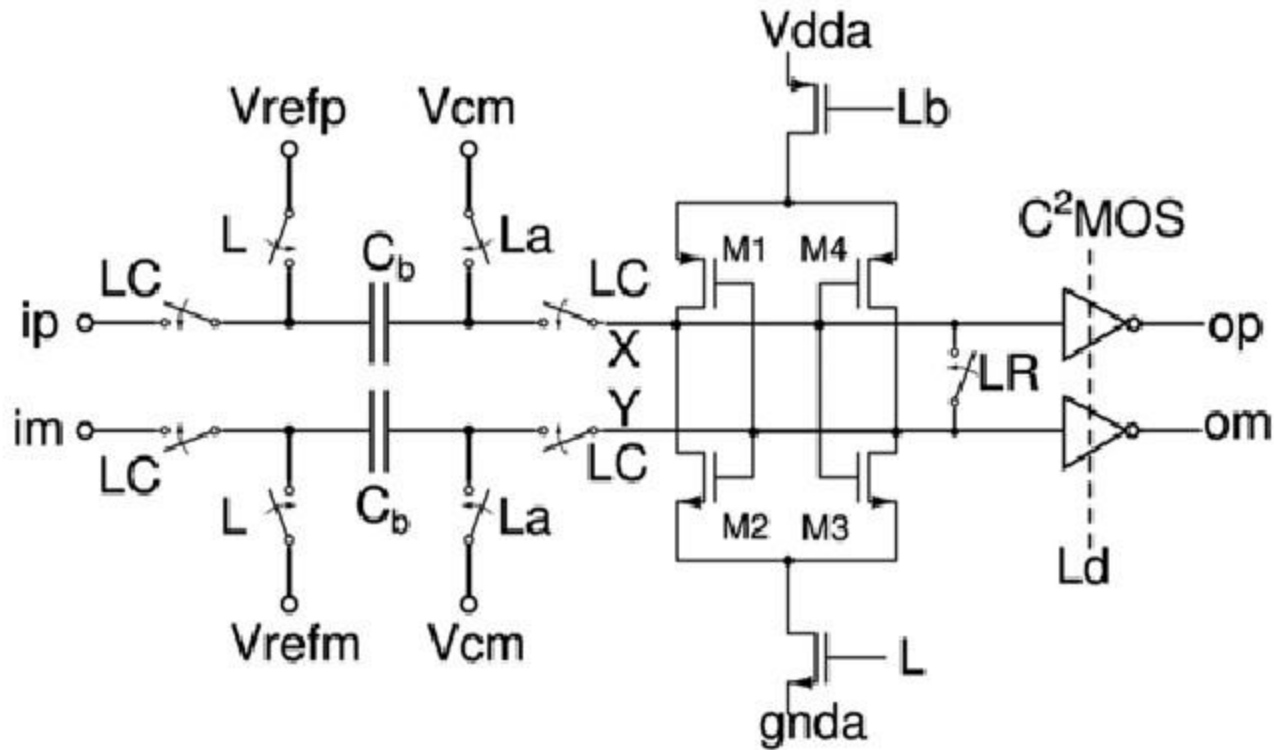
# Current-Steering/CML Latch



- Current mode logic (CML) latch
- Constant current  $\rightarrow$  supply very quiet
- Higher gain in tracking mode
- Cannot produce full logic levels
- Fast
  - Popular for high-speed designs
- Trip point of the inverters

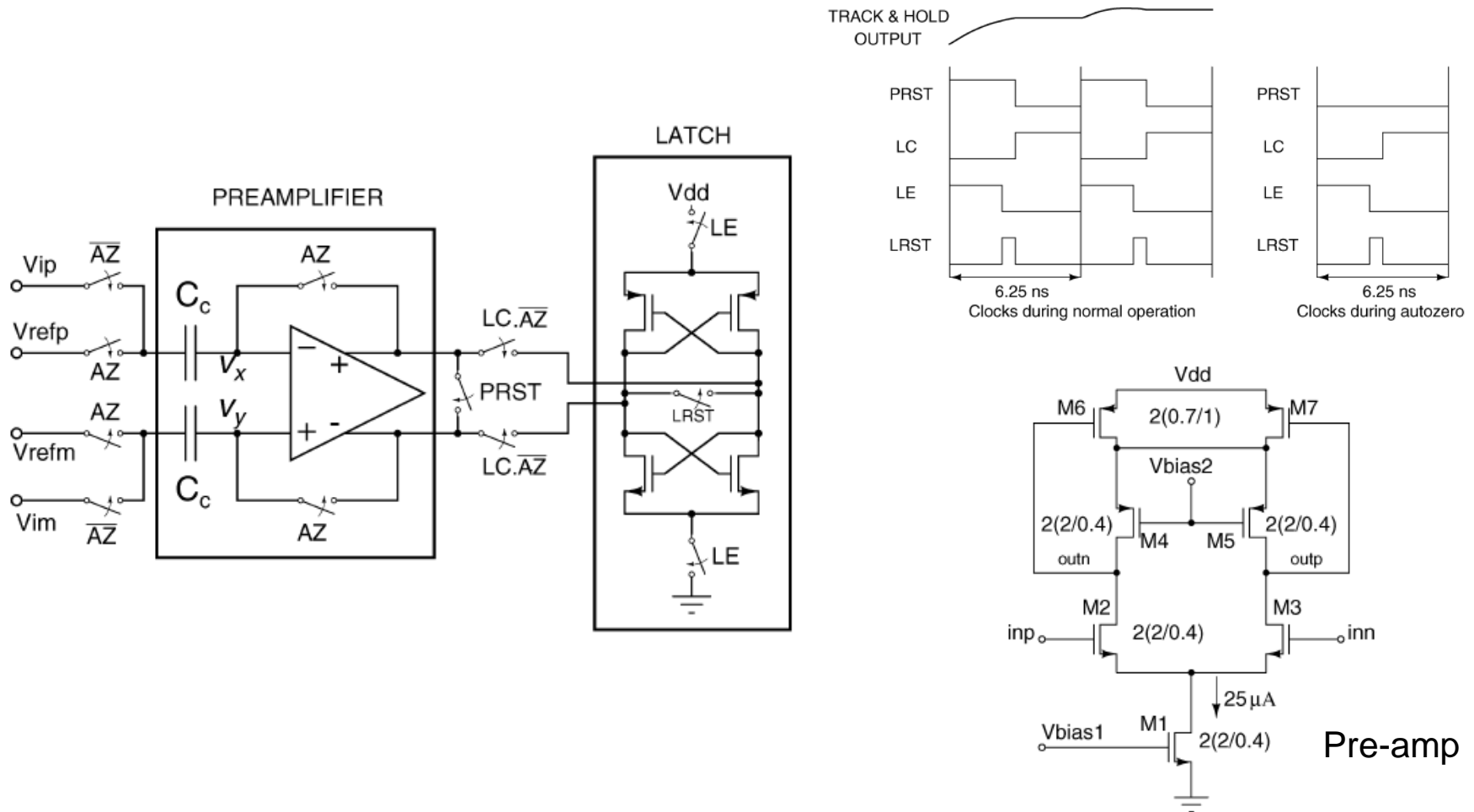


# Reference Subtraction



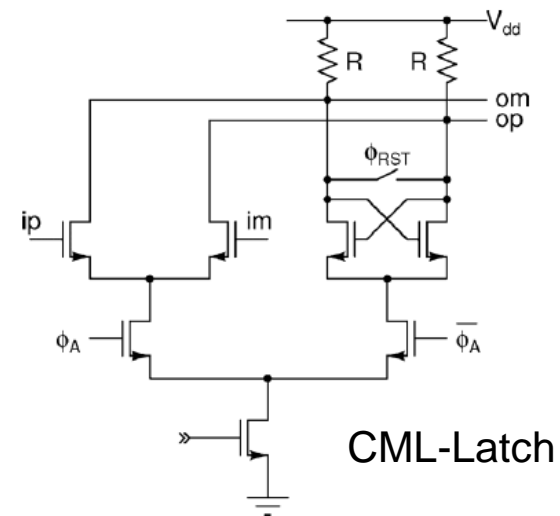
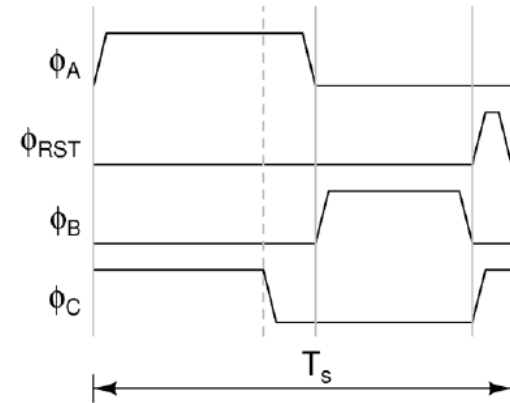
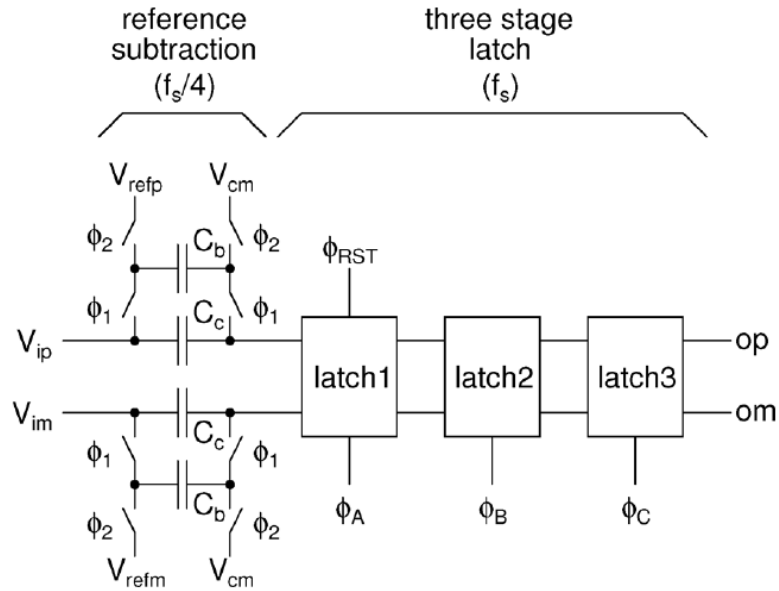
S. Pavan, N. Krishnapura, R. Pandarinathan, P. Sankar, "A Power Optimized Continuous-time Delta-Sigma Modulator for Audio Applications," IEEE JSSC, vol. 43, no. 2, pp. 351-360, Feb. 2008.

# Autozeroing and Reference Subtraction



V. Srinivas, S. Pavan, A. Lachhwani, and N. Sasidhar, "A Distortion Compensating Flash Analog-to-Digital Conversion Technique," IEEE JSSC, vol. 41, no. 9, pp. 1959-1969, Sep. 2006.

# CML based Comparator



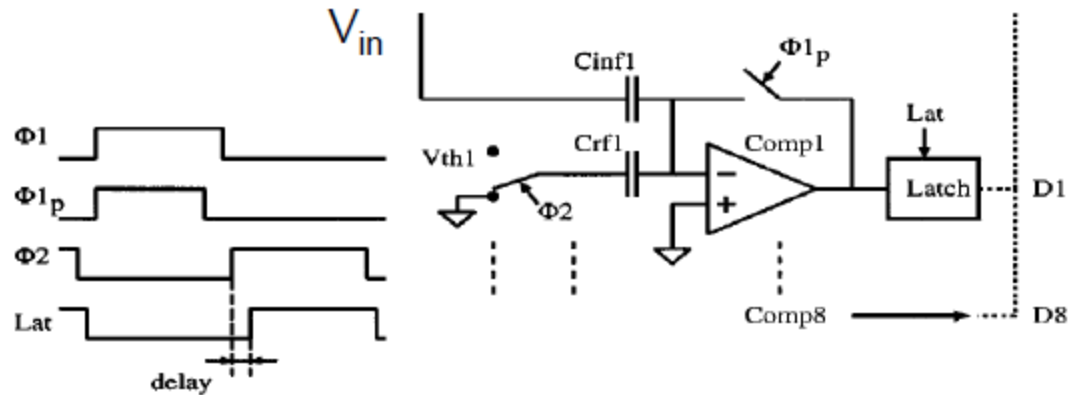
V. Singh, N. Krishnapura, S. Pavan, B. Vignanam, D. Behera, and N. Nigania, "A 16MHz BW 75 dB DR CT  $\Delta\Sigma$  ADC Compensated for More Than One Cycle Excess Loop Delay," IEEE JSSC, vol. 47, no. 8, Aug. 2012.



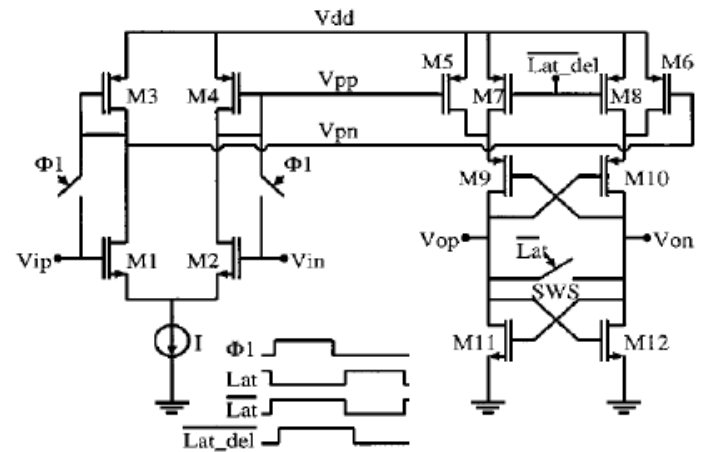
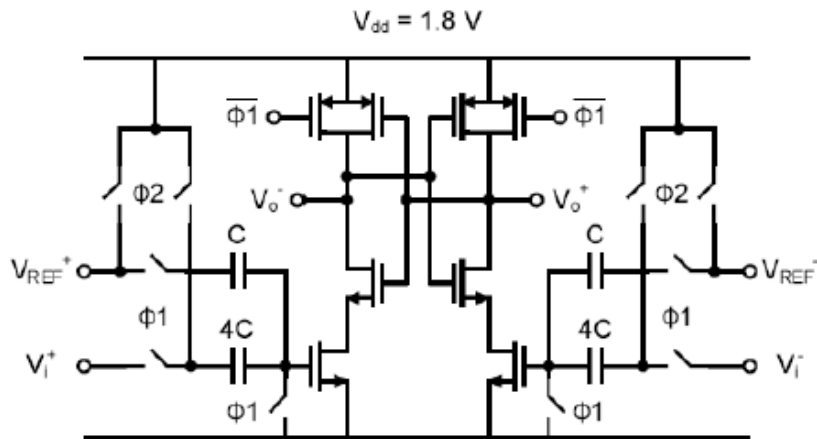
# Comparators for Pipelined ADCs

- ❑ Pipelined ADCs employ at least 0.5 bit/stage redundancy
  - Can tolerate large offsets and large noise with appropriate redundancy
  
- ❑ Should consume negligible power in a good design
  - 50-100 mW or less per comparator
  
- ❑ Lots of implementation options
  - Resistive/capacitive reference generation
  - Different pre-amp/latch topologies

# Comparators for Pipelined ADCs

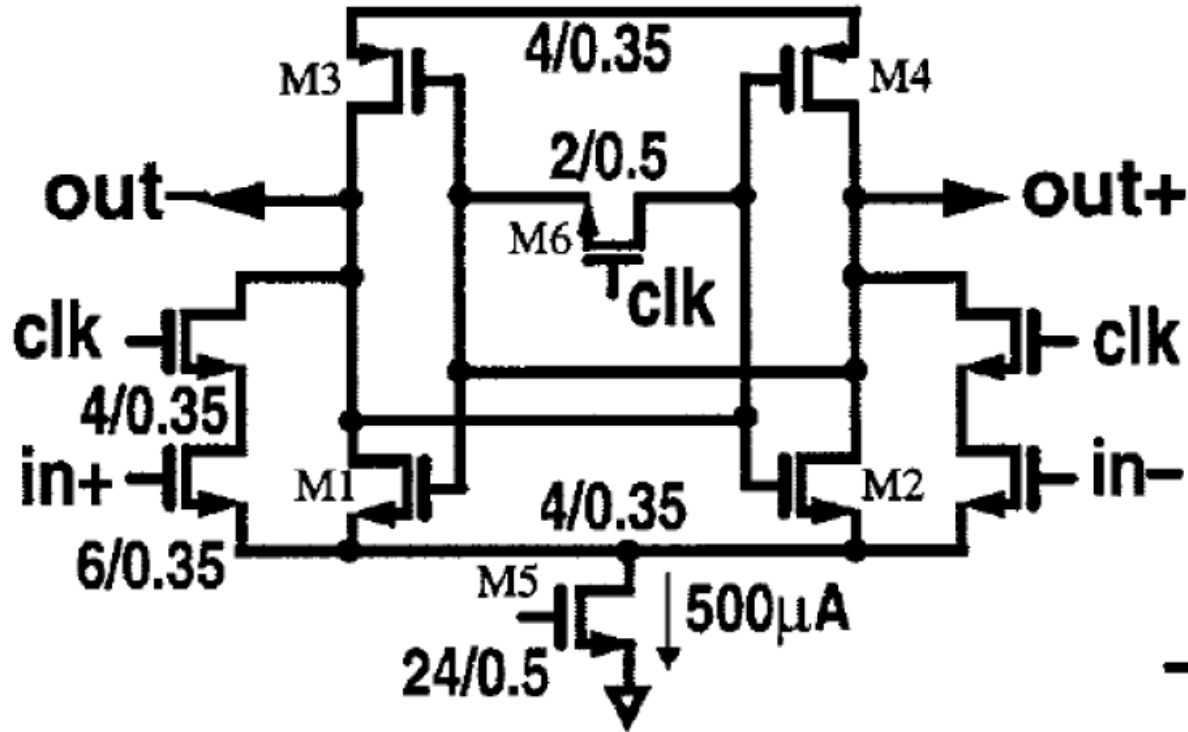


[Chiu 2004]



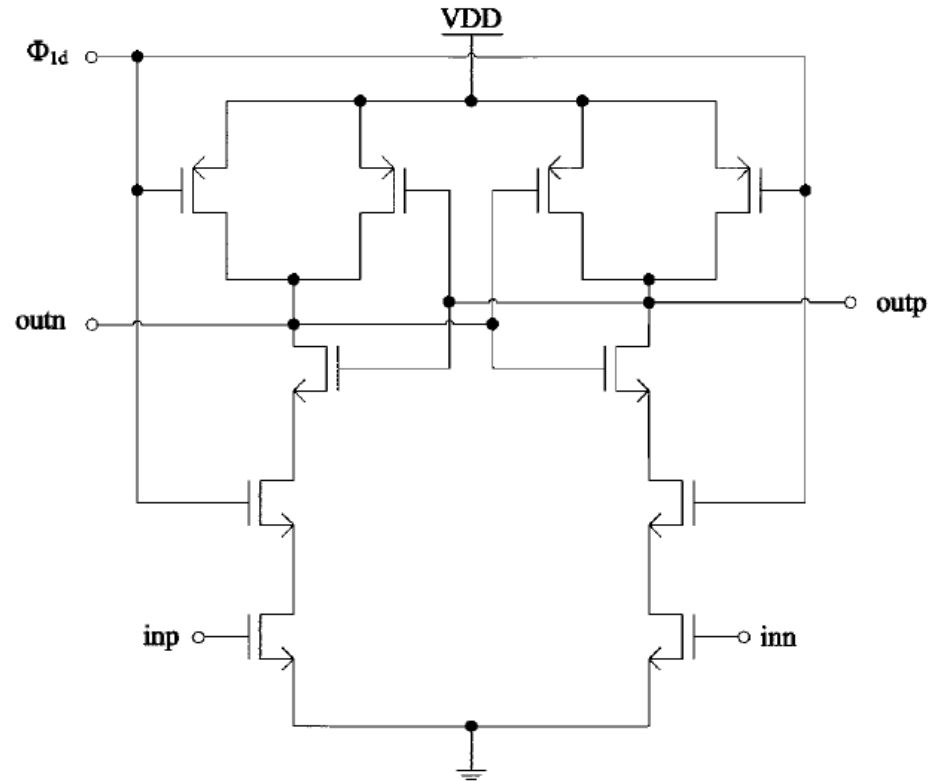
[Mehr 2000]

# Comparator Example



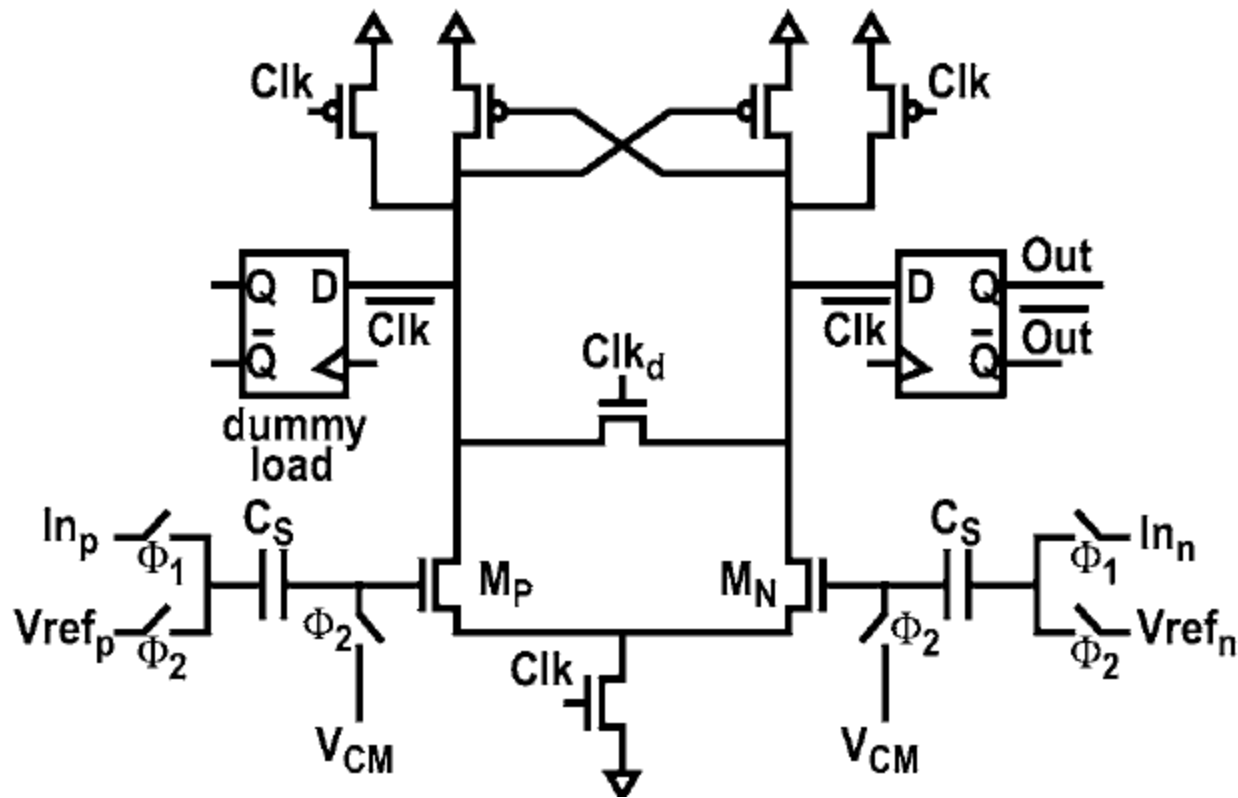
A 6-b 1.3-Gsample/s A/D Converter in 0.35- $\mu m$  CMOS  
IEEE JSSC, vol. 36, no. 12, Dec 2001.

# Latch Example



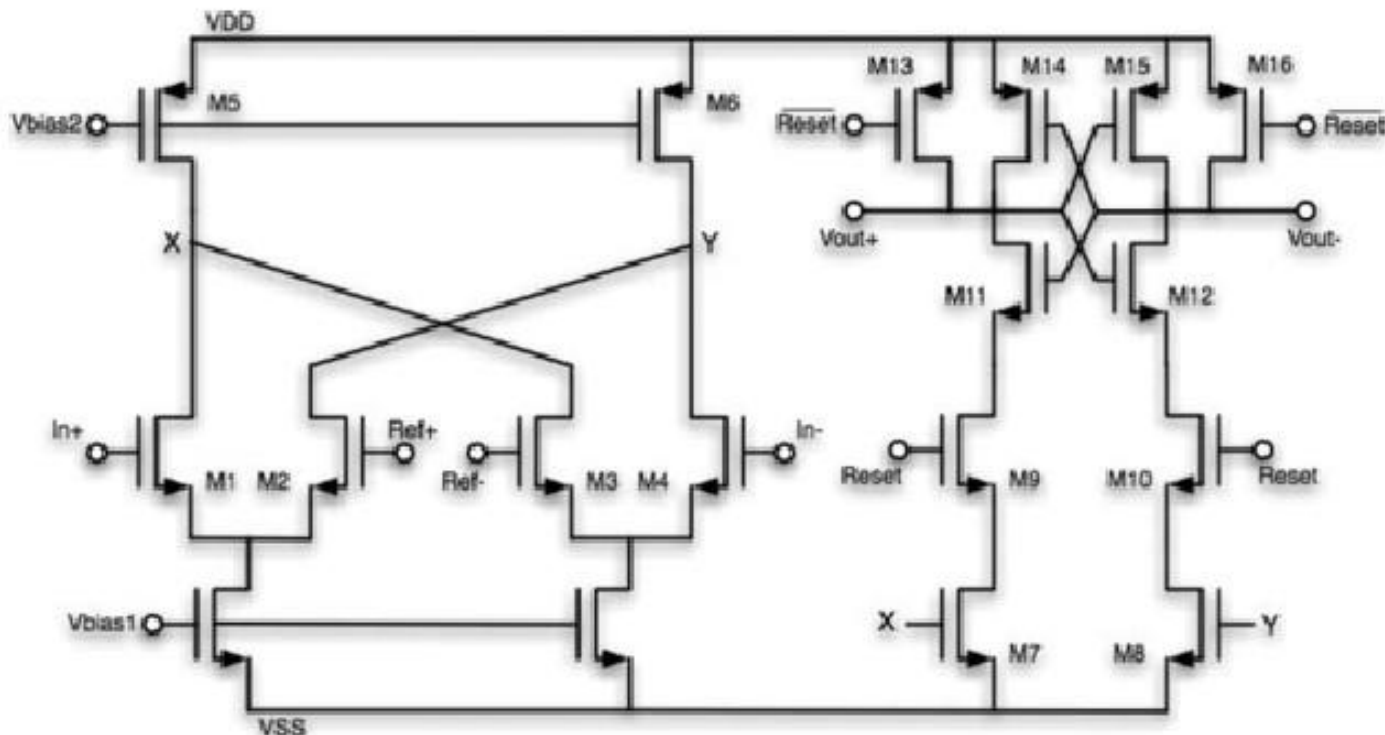
A 0.9-V 60-W 1-Bit Fourth-Order Delta-Sigma Modulator With 83-dB Dynamic Range  
IEEE JSSC, vol. 43, no. 2, Feb. 2008

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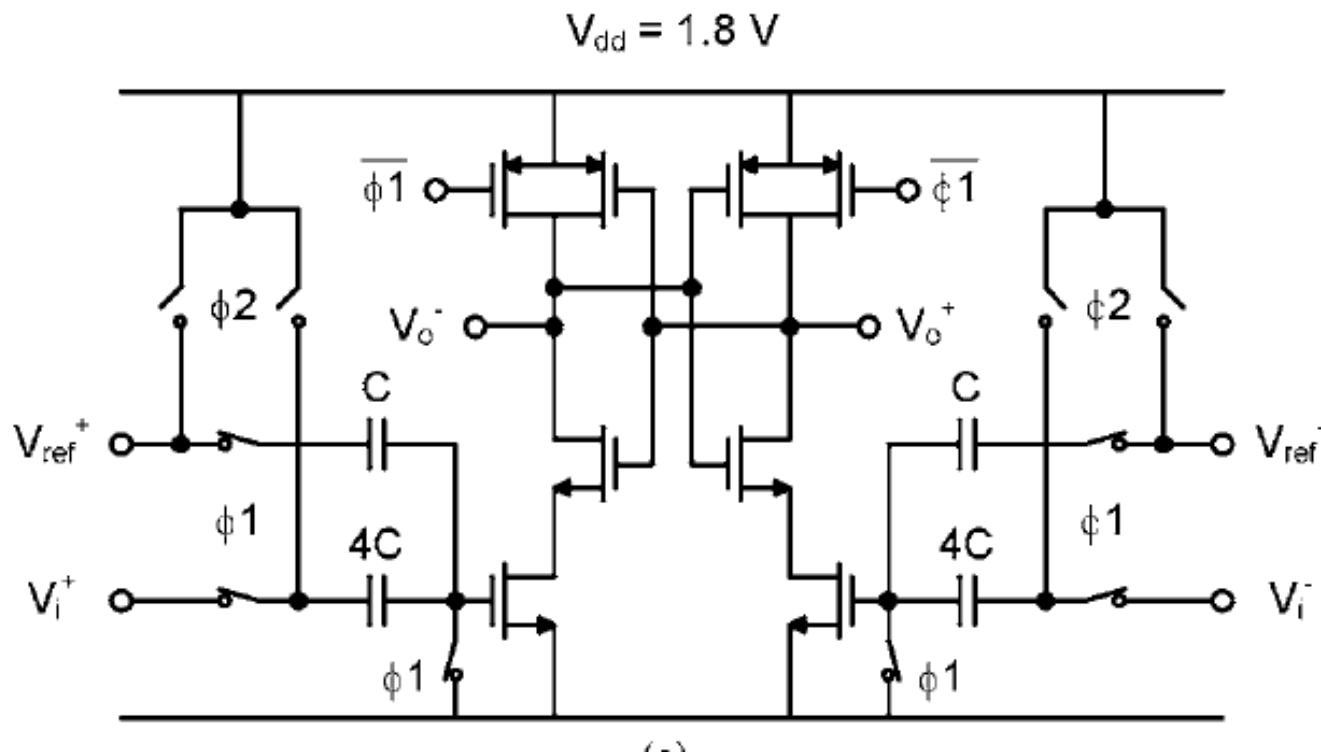
A 77-dB Dynamic Range, 7.5-MHz Hybrid Continuous-Time/Discrete-Time Cascaded  $\Delta\Sigma$  Modulator, IEEE JSSC, vol. 43, no. 4, Apr 2008

# Comparator Example



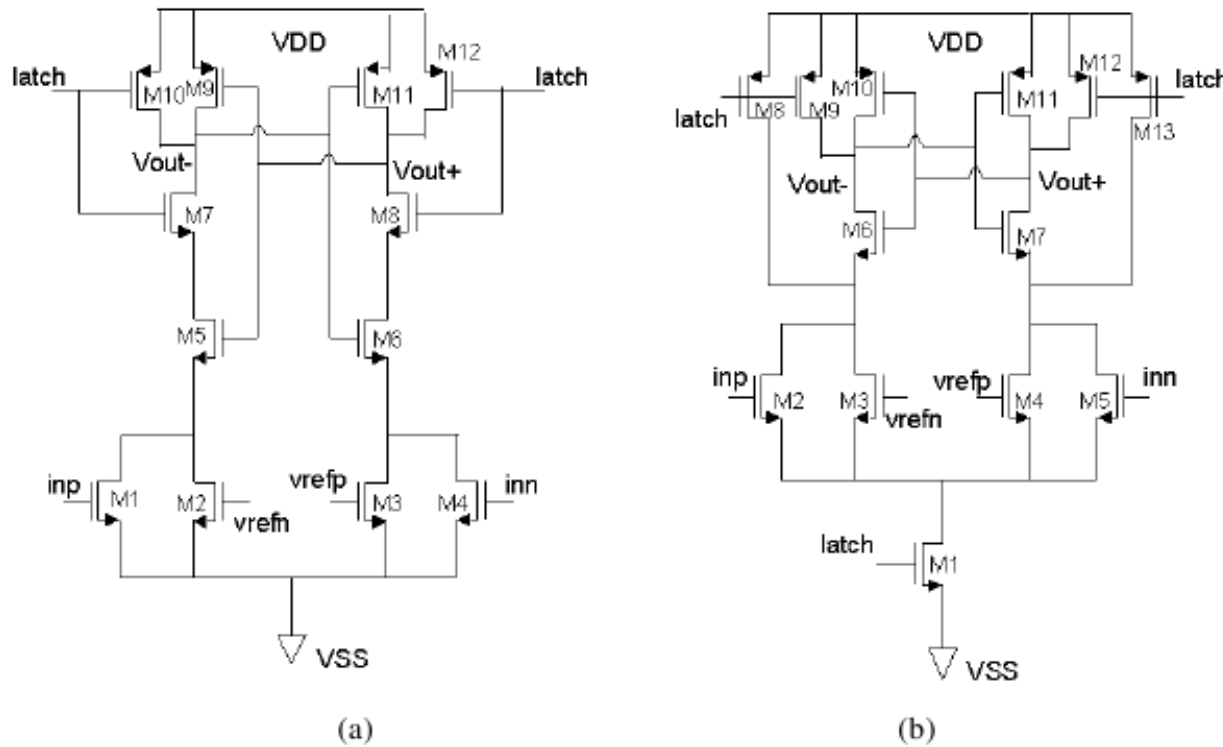
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Y. Chiu, P. R. Gray, and B. Nikolic, "A 14-b 12-MS/s CMOS pipeline ADC with over 100-dB SFDR," IEEE JSSC, vol. 39, pp. 2139 - 2151, December 2004.

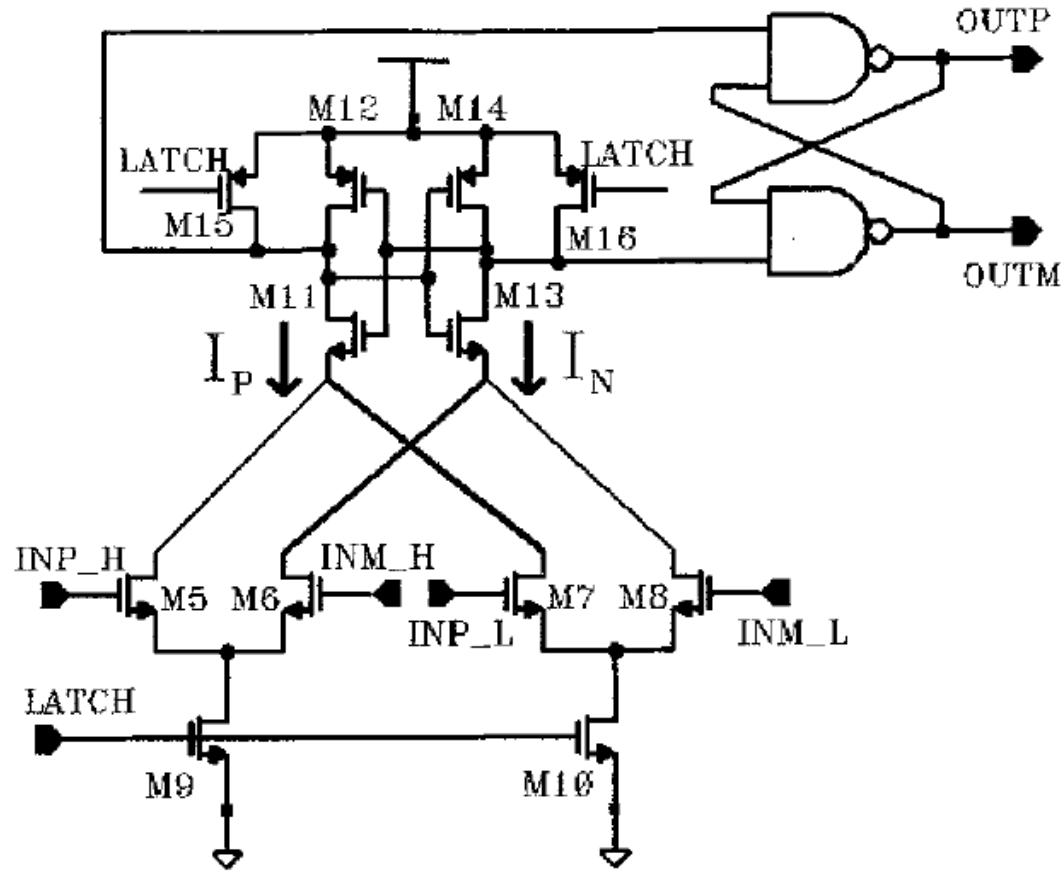
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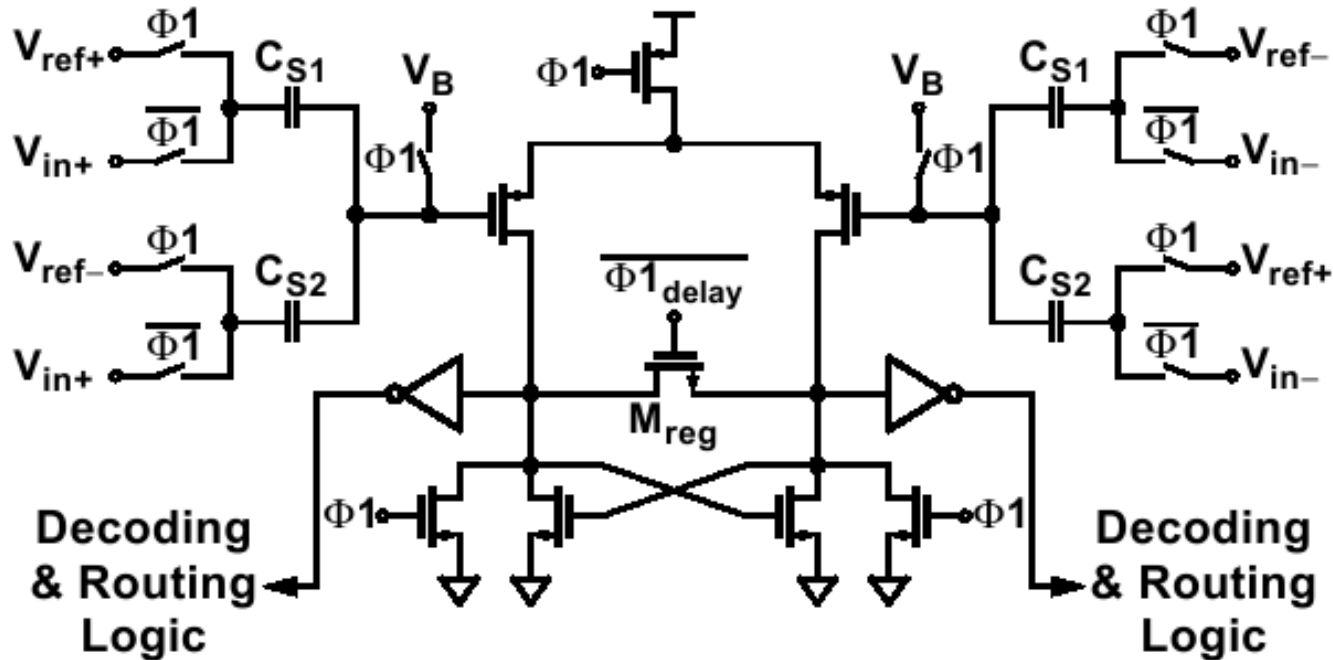


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# Exercise

- Compare the latches with respect to
  - Static power dissipation
  - Dynamic and static Offsets
  - Kickback noise at the input
  - Number of clock phases
  - Maximum achievable clock speed

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